

Title (en)
Three-dimensional integrated circuit and manufacturing method therefor.

Title (de)
Dreidimensionale integrierte Schaltung und deren Herstellungsverfahren.

Title (fr)
Circuit intégré tridimensionnel et son procédé de fabrication.

Publication
EP 0238089 A2 19870923 (EN)

Application
EP 87104091 A 19870320

Priority
• JP 6298186 A 19860320
• JP 11647086 A 19860520

Abstract (en)
The invention relates to a three-dimensional IC stacked on a base plate comprising a unit semiconductor IC, A, which has each constituent IC (2a, 2b) either on a surface or on both surfaces of a substrate (1). The unit semiconductor IC has a plurality of conducting posts (4), buried in and penetrating through the substrate (1) and insulated therefrom, and also interconnection terminals (6, 7) on both sides of the substrate for connecting another unit semiconductor IC or the base plate. By stacking plural unit ICs on the base plate, a very large-scale IC can be fabricated. each constituent IC is formed on a bulk silicon substrate, so that excellent quality can be obtained. The invention can also be used for the fabrication of ROM structure such as a PROM or MASK ROM, using a single unit semiconductor IC, wherein a wiring for the ROM can be formed on a bottom surface of the substrate.

IPC 1-7
H01L 25/08; **H01L 21/74**; **H01L 21/312**

IPC 8 full level
H01L 21/768 (2006.01); **H01L 23/48** (2006.01); **H01L 25/065** (2006.01)

CPC (source: EP KR US)
H01L 21/6835 (2013.01 - EP US); **H01L 21/76898** (2013.01 - EP KR US); **H01L 23/481** (2013.01 - EP KR US);
H01L 25/0657 (2013.01 - EP KR US); **H01L 25/50** (2013.01 - EP US); **H01L 27/0694** (2013.01 - EP US); **H01L 27/0688** (2013.01 - EP);
H01L 2221/6835 (2013.01 - EP US); **H01L 2221/68363** (2013.01 - EP US); **H01L 2224/16** (2013.01 - EP KR US);
H01L 2225/06524 (2013.01 - EP KR US); **H01L 2225/06541** (2013.01 - EP KR US); **H01L 2225/06596** (2013.01 - EP US);
H01L 2924/01014 (2013.01 - EP US); **H01L 2924/01019** (2013.01 - EP US); **H01L 2924/01079** (2013.01 - EP US);
H01L 2924/13091 (2013.01 - EP US); **H01L 2924/19041** (2013.01 - EP US)

C-Set (source: EP US)
H01L 2924/13091 + **H01L 2924/00**

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Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
EP 0238089 A2 19870923; **EP 0238089 A3 19871111**; **EP 0238089 B1 19920513**; DE 3778944 D1 19920617; KR 870009472 A 19871027;
KR 900008647 B1 19901126; US 4939568 A 19900703

DOCDB simple family (application)
EP 87104091 A 19870320; DE 3778944 T 19870320; KR 870002514 A 19870319; US 32512289 A 19890317